



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants: Constantin Bulucea and Rebecca Rossen

Assignee: Siliconix incorporated

Title: Trench DMOS Power Transistor With Field-Shaping Body Profile and Three-Dimensional Geometry

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PRELIMINARY AMENDMENT

Sir:

Please amend the above patent application as follows:

IN THE CLAIMS

Amend Claims 17 - 23, 25, 26, 29 - 42, 46 - 48, and 52 - 65 to read as follows with unchanged Claims 27, 28, 44, and 49 - 51 being repeated below for the Examiner's convenience:

H H

--17. (Four times amended) A trench DMOS transistor cell comprising:
a substrate of a first conductivity type, said substrate having a surface;
an epitaxial layer of said first conductivity type formed on said surface of said substrate, said epitaxial layer having a top surface and a bottom surface, said epitaxial layer having a substantially uniform initial dopant concentration at formation;
a body region of a second conductivity type opposite to said first conductivity type formed in said epitaxial layer, said body region extending, as measured from said top surface of said epitaxial layer, to a first depth d_{max} at a first location and to a depth d at a second

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